

General Purpose Transistor

Comchip
SMD Diode Specialist

2N3904-HF (NPN)

RoHS Device

Halogen Free

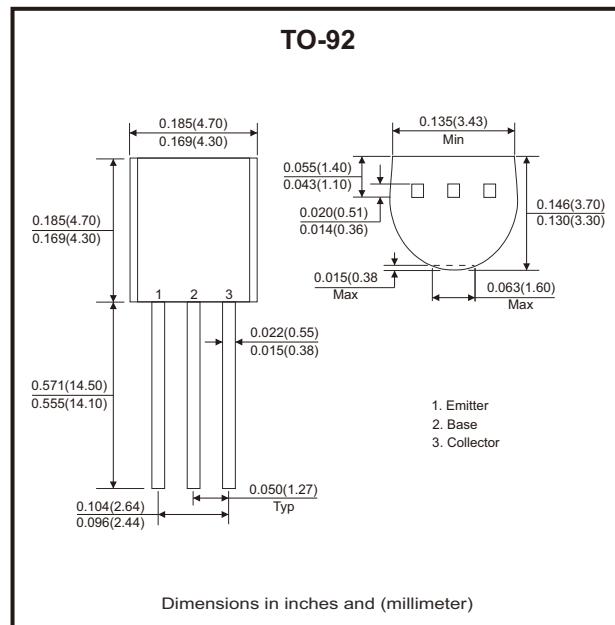


Features

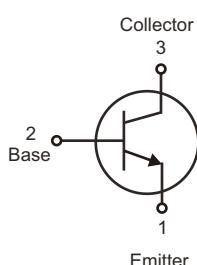
- NPN silicon epitaxial planar transistor for switching and amplifier applications.

Mechanical Data

- Case: TO-92, molded plastic.
- Mounting position: Any.



Circuit Diagram



Maximum Ratings (at Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-base voltage	V _{CBO}	60	V
Collector-emitter voltage	V _{CEO}	40	V
Emitter-base voltage	V _{EBO}	6	V
Collector current-continuous	I _C	0.2	A
Collector power dissipation	P _C	0.625	W
Operation junction and storage temperature range	T _J , T _{STG}	-55 to +150	°C

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Electrical Characteristics (at $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_C = 10\mu\text{A}, I_E = 0$	60			V
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = 1\text{mA}, I_B = 0$	40			V
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_E = 10\text{mA}, I_C = 0$	6			V
Collector cut-off current	I_{CBO}	$V_{\text{CB}} = 60\text{V}, I_E = 0$			0.1	μA
Collector cut-off current	I_{CEX}	$V_{\text{CE}} = 30\text{V}, V_{\text{EB}(\text{off})} = 3\text{V}$			0.05	μA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}} = 5\text{V}, I_C = 0$			0.1	μA
DC current gain	$h_{\text{FE}(1)}$	$V_{\text{CE}} = 1\text{V}, I_C = 10\text{mA}$	100		400	
	$h_{\text{FE}(2)}$	$V_{\text{CE}} = 1\text{V}, I_C = 50\text{mA}$	60			
	$h_{\text{FE}(3)}$	$V_{\text{CE}} = 1\text{V}, I_C = 100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	$I_C = 50\text{mA}, I_B = 5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{\text{CE}} = 20\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$	300			MHz
Delay time	t_d	$V_{\text{CC}} = 3\text{V}, V_{\text{BE}} = 0.5\text{V}, I_C = 10\text{mA}, I_{B1} = 1\text{mA}$			35	nS
Rise time	t_r				35	nS
Storage time	t_s	$V_{\text{CC}} = 3\text{V}, I_C = 10\text{mA}, I_{B1} = I_{B2} = 1\text{mA}$			200	nS
Fall time	t_f				50	nS

Classification of $h_{\text{FE}}(1)$

Rank	O	Y	G
Range	100-200	200-300	300-400

Typical Rating and Characteristic Curves (2N3904-HF)

Fig.1 - Static Characteristic

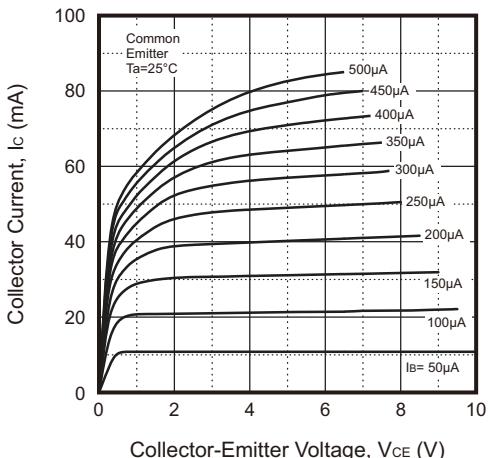
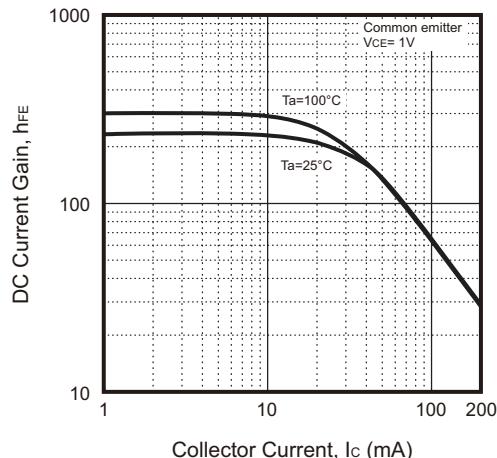
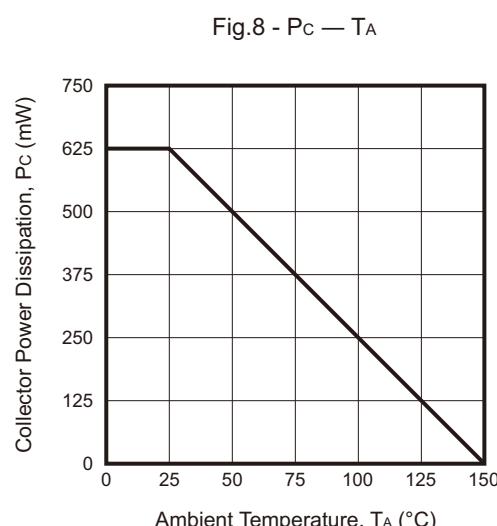
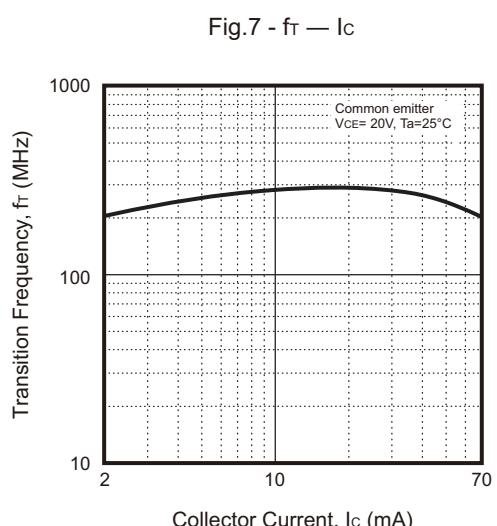
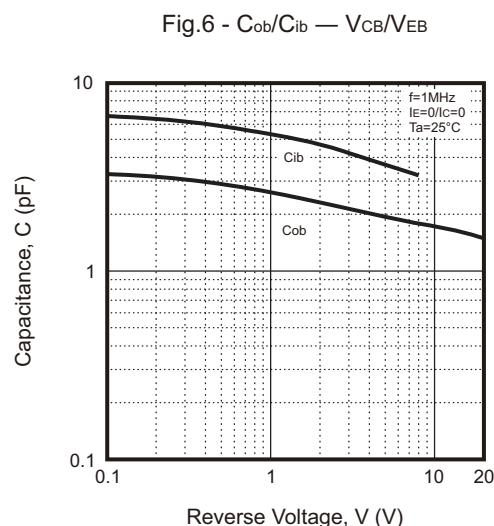
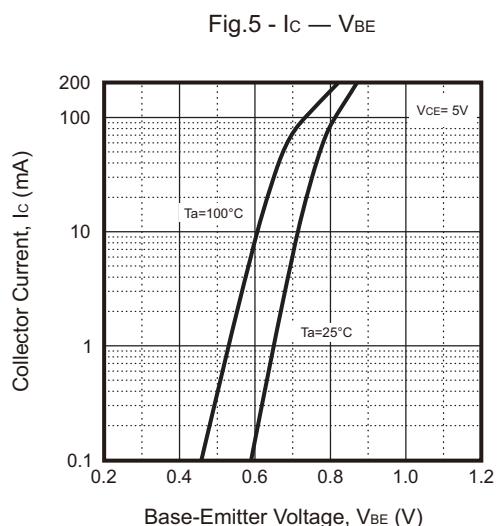
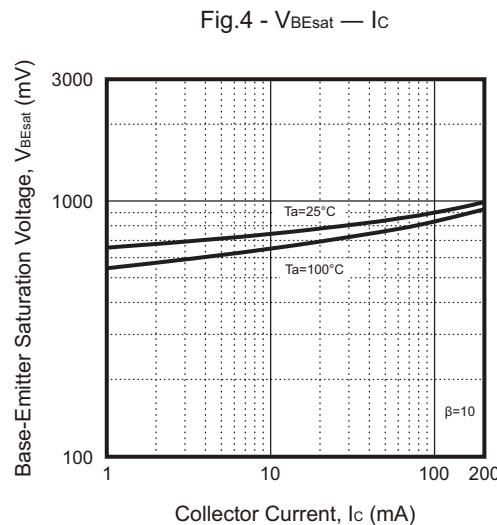
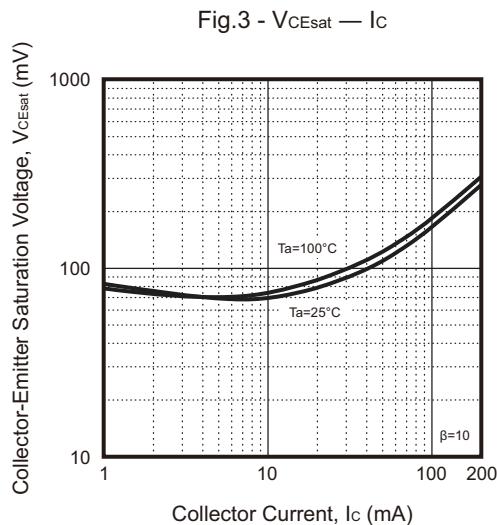


Fig.2 - $h_{\text{FE}} — I_C$



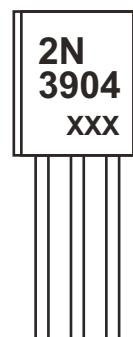
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Typical Rating and Characteristic Curves (2N3904-HF)



Marking Code

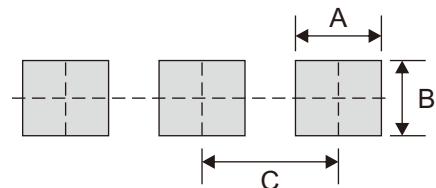
Part Number	Marking Code
2N3904-HF	2N3904



XXX = Control code

Suggested P.C.B. PAD Layout

SIZE	TO-92	
	(mm)	(inch)
A	0.80	0.031
B	0.70	0.028
C	1.27	0.050



Standard Packaging

Case Type	BULK PACK
	BAG (pcs)
TO-92	1,000